

# High Voltage Transistors

## NPN Silicon



# MMBT5550L, MMBT5551L

### Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5550 MMBT5551	$V_{CEO}$	140 160	Vdc
Collector – Base Voltage MMBT5550 MMBT5551	$V_{CBO}$	160 180	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	600	mAdc
Electrostatic Discharge Human Body Model Machine Model	ESD	> 8000 > 400	V

### THERMAL CHARACTERISTICS

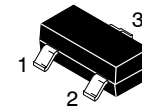
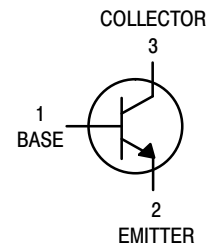
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) @ $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

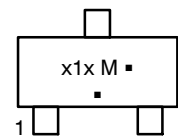
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SOT-23 (TO-236)  
CASE 318  
STYLE 6

### MARKING DIAGRAM



x1x = Device Code  
M1F = MMBT5550LT  
G1 = MMBT5551LT

M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MMBT5550LT1G, NSVMMBT5550LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5550LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT5550L, MMBT5551L

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage (Note 3) ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	MMBT5550 MMBT5551	$V_{(BR)CEO}$	140 160	– –	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100\ \mu\text{Adc}$ , $I_E = 0$ )	MMBT5550 MMBT5551	$V_{(BR)CBO}$	160 180	– –	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10\ \mu\text{Adc}$ , $I_C = 0$ )		$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ , $T_A = 100^\circ\text{C}$ ) ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ , $T_A = 100^\circ\text{C}$ )	MMBT5550 MMBT5551 MMBT5550 MMBT5551	$I_{CBO}$	– – – –	100 50 100 50	nAdc $\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	–	50	nAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )  ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )  ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551	$h_{FE}$	60 80 60 80 20 30	– – 250 250 – –	–
Collector – Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	Both Types MMBT5550 MMBT5551	$V_{CE(sat)}$	– – –	0.15 0.25 0.20	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	Both Types MMBT5550 MMBT5551	$V_{BE(sat)}$	– – –	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off ( $V_{CB} = 10\text{ V}$ ) ( $V_{CB} = 75\text{ V}$ )	Both Types	$I_{CES}$	– –	50 100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2.0%.

# MMBT5550L, MMBT5551L

## TYPICAL CHARACTERISTICS

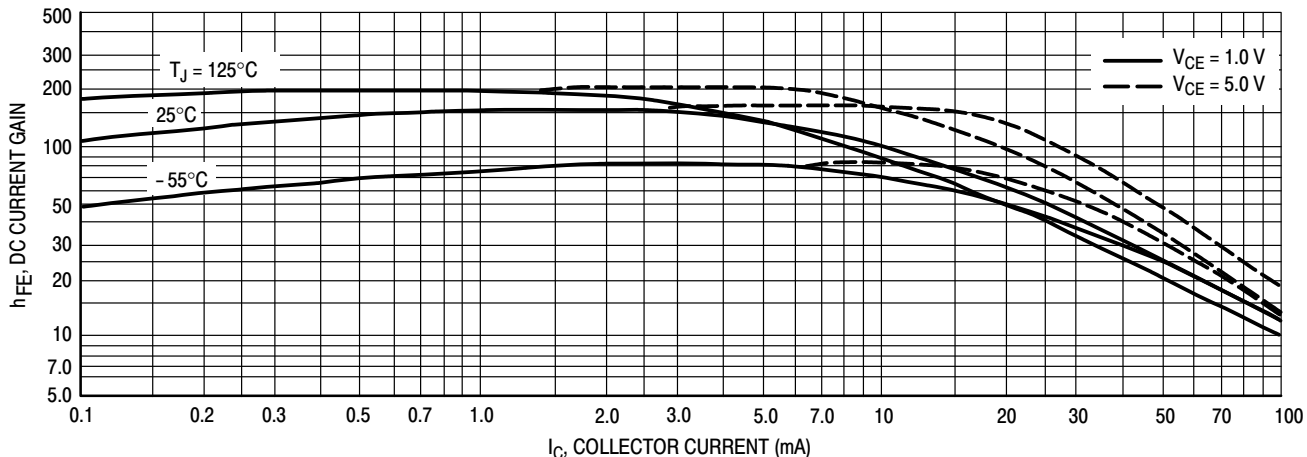


Figure 1. DC Current Gain

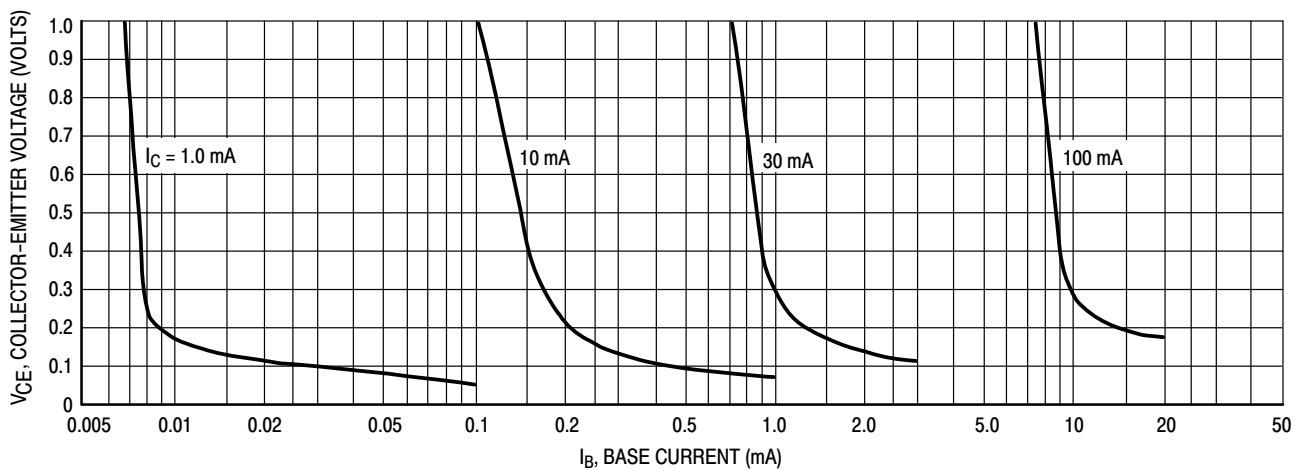


Figure 2. Collector Saturation Region

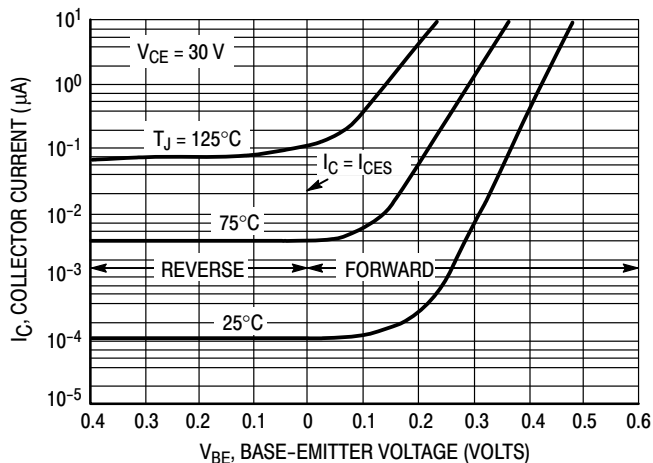


Figure 3. Collector Cut-Off Region

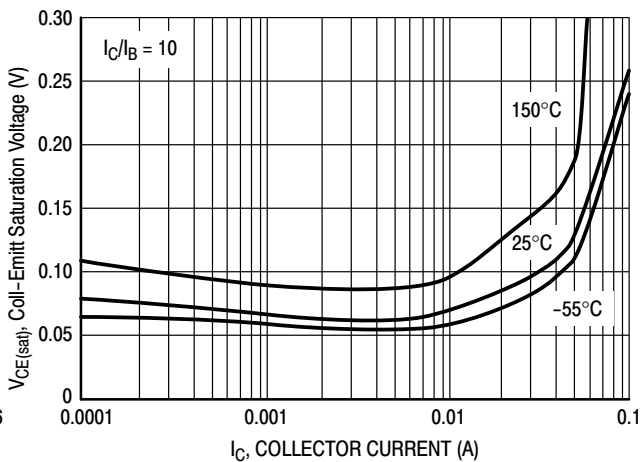


Figure 4.  $V_{CE(sat)}$

# MMBT5550L, MMBT5551L

## TYPICAL CHARACTERISTICS

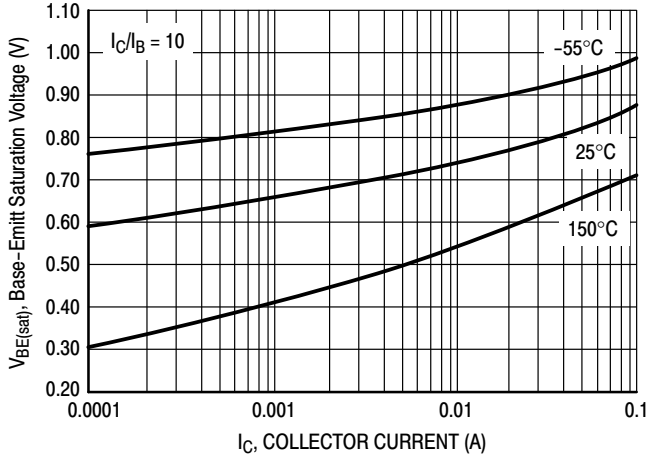


Figure 5.  $V_{BE(sat)}$

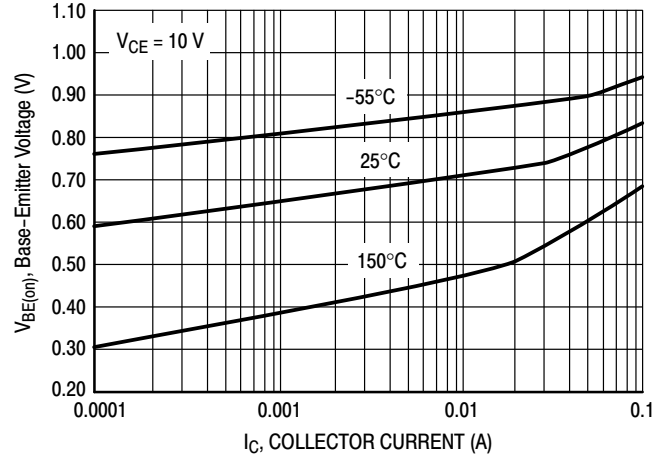


Figure 6.  $V_{BE(on)}$

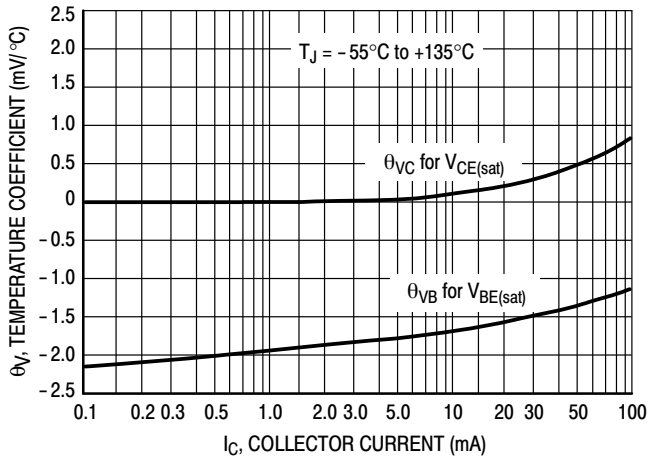


Figure 7. Temperature Coefficients

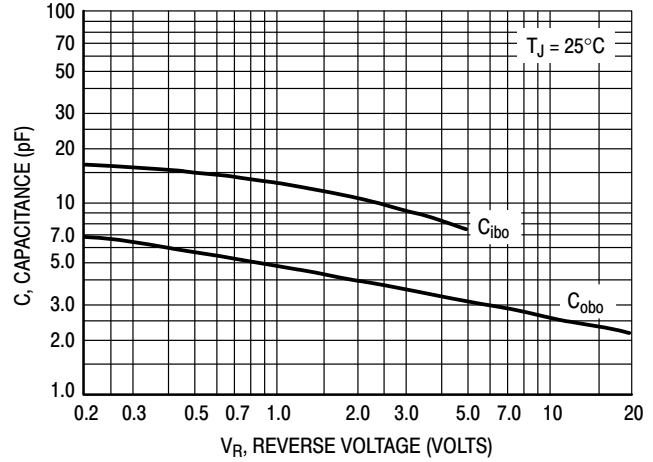
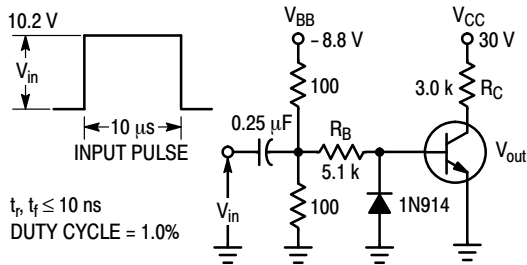


Figure 8. Capacitances



Values Shown are for  $I_C @ 10 \text{ mA}$

Figure 9. Switching Time Test Circuit

# MMBT5550L, MMBT5551L

## TYPICAL CHARACTERISTICS

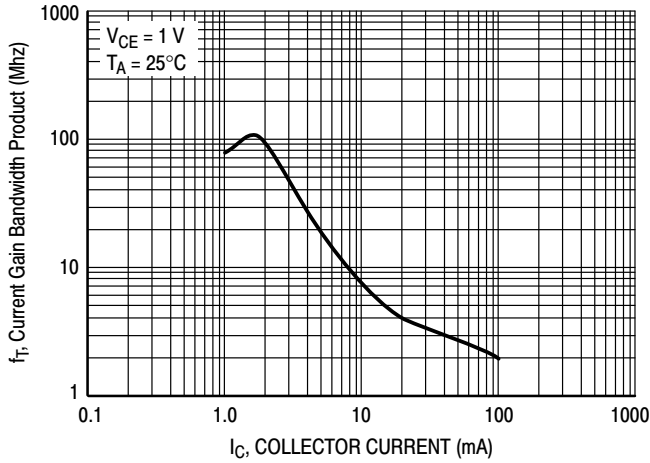


Figure 10. Current Gain Bandwidth Product

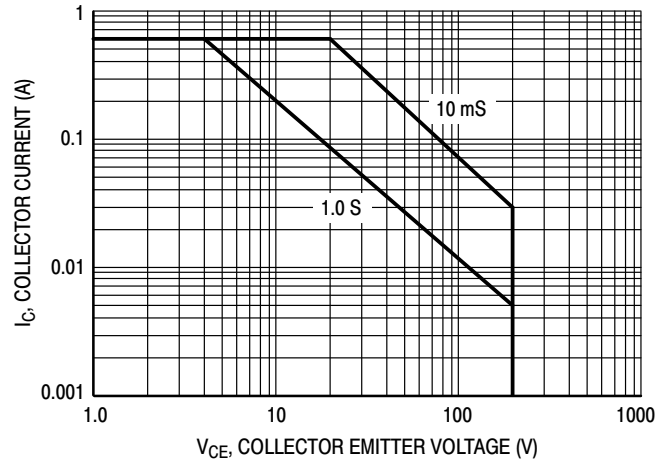


Figure 11. Safe Operating Area

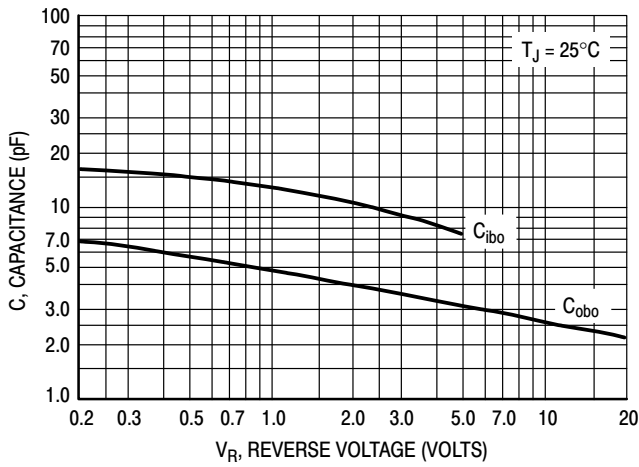


Figure 12. Capacitances

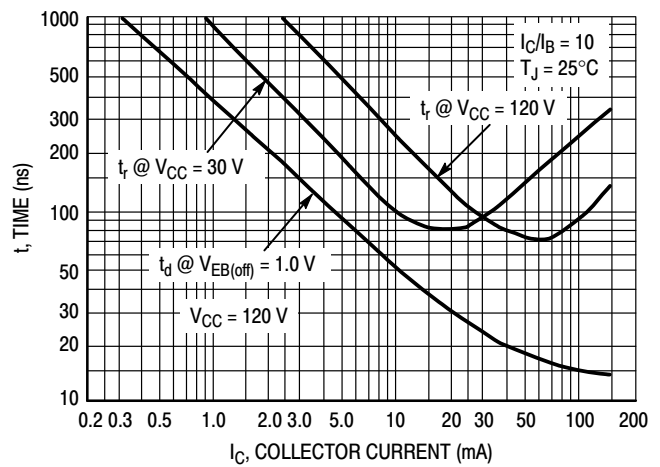


Figure 13. Turn-On Time

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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